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PATENT

Attorney Docket No. 5308

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler et al.

Serial No.: 10/617,843

Filed: July 11, 2003

For: NITRIDE-BASED TRANSISTORS AND METHODS OF FABRICATION THEREOF
USING NON-ETCHED CONTACT RECESSES

Group Art Unit: 2823

Examiner: Fernando L. Toledo

Confirmation No.: 7985

Date: July 8, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

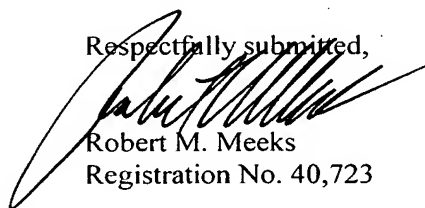
FIFTH INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the waiver by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(i) for all U.S. national patent applications filed after June 30, 2003 and for all international applications that have entered the national stage under 35 USC § 371 after June 30, 2003.

It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP. No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

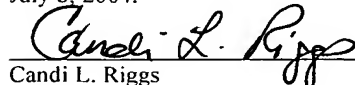
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| FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office | | | | Attorney Docket Number: 5308-248 | | Serial No.: 10/617,843 | |
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| LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary) | | | | Applicants: Saxler et al. | | | |
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EXAMINER

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